

ABSTRACT

A method for adapting to specific needs an integrated circuit having a stack of insulating layers, each layer being associated with a determined metallization level, metal areas of the last metallization level forming electric contacts of the integrated circuit,
5 including the steps of forming pairs of metal regions of the penultimate metallization level having a facing edge and connected to components of the integrated circuit; depositing an insulating layer; etching according to the specific needs the insulating layer to expose the facing edges of the metal regions of determined pairs; and forming metal portions of the last metallization level which cover the facing edges of the metal regions
10 of all pairs and which contact the metal regions of the determined pairs.